

3kW Power Supply for AI Servers Using Surface-Mounted SiC MOSFET

Reference Guide

RD265-RGUIDE-01

Toshiba Electronic Devices & Storage Corporation



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1. Introduction

This reference guide describes the specifications, usage, and characteristics of the 3kW power supply for Al servers with surface mounted SiC MOSFETs (hereafter referred to as "this design").

The rapid advancement and widespread adoption of generative AI technologies have led to increased demand for AI servers capable of executing high-speed processing. AI servers are equipped with multi-core accelerators such as GPUs (Graphics Processing Units) and NPUs (Neural Processing Units), which are optimized for matrix operations commonly used in AI workloads. While these systems offer exceptional computational performance, they also require substantial electrical power. As a result, AI server power supplies are required to deliver higher efficiency, higher power output, and more compact form factors, making high power density essential. This design accepts an AC input voltage range of 180 to 264V and outputs DC 50V through a semi-bridgeless PFC (Power Factor Correction) circuit and a Phase Shift Full Bridge (PSFB) circuit. The maximum output power is 3kW when using an AC 200V input. It includes an output ORing circuit that enables redundant operation, as well as an internal auxiliary power supply circuit required for powering internal control circuits. By separating the power devices from the main board, the footprint per output is reduced, contributing to a more compact power supply.

This design uses the SiC MOSFET $\underline{TW092V65C}$ and the SiC Schottky Barrier Diode $\underline{TRS12V65H}$ in the semi-bridgeless PFC circuit. The PSFB circuit uses the SiC MOSFET $\underline{TW027U65C}$ with integrated Schottky Barrier Diode on the primary full-bridge side, and the power MOSFET $\underline{TPW2900ENH}$ on the secondary synchronous rectification side. For isolated gate signal transmission from the secondary-side controller, the digital isolator $\underline{DCL540C01}$ is used. The output ORing circuit uses the power MOSFET $\underline{TPM1R908QM}$. By integrating these advanced Toshiba devices, this design achieves high efficiency equivalent to 80PLUS Platinum level ($V_{in} = 230V$, $P_{out} = 3kW$) in a compact form factor.

Note:

80 PLUS is an efficiency certification standard for computer power supply units, including those used in servers.



2. Appearance and Specifications

2.1. Specifications

Table 2.1 lists the input and output characteristics of this design.

Table 2.1 Specifications

Parameters	Conditions	Min.	Тур.	Max.	Unit			
Input Characteristics								
AC input voltage (rms)		180		264	V			
AC input current (rms)	V _{in} = AC 90V, I _{out} = 30A			18.5	Α			
Input frequency		47		63	Hz			
Internal Characteristics (Semi-Bridgeless PFC Circuit)								
Output voltage			390		V			
Output power	V _{in} = AC 230V			3	kW			
Switching frequency			100		kHz			
Output Characteristics (PSFB Circuit)								
Output voltage			50		V			
Output current	V _{in} = AC 230V			60	Α			
Output power	V _{in} = AC 230V			3	kW			
Output ripple voltage	T _a = 25℃			500	mV			
Switching frequency			130		kHz			
Other								
Protection	Output Overvoltage Protection, Output Overcurrent Protection							
	Output Short-Circuit Protection, Overtemperature Protection							
	Main Board: FR-4, 6-Layers (through-hole via), 1.6mm							
	Cu Thickness 70μm (outer layers), 35μm (inner layers)							
Substrate structure	PFC Board: FR-4, 6-Layers (resin-filled via), 1.0mm							
Substrate structure	Cu Thickness 70μm (outer layers), 35μm (inner layers)							
	Main Board: FR-4, 6-Layers (resin-filled via), 1.0mm							
	Cu Thickness 70μm (outer layers), 35μm (inner layers)							

2.2. Block Diagram

Fig. 2.1 shows a block diagram to understand the function.

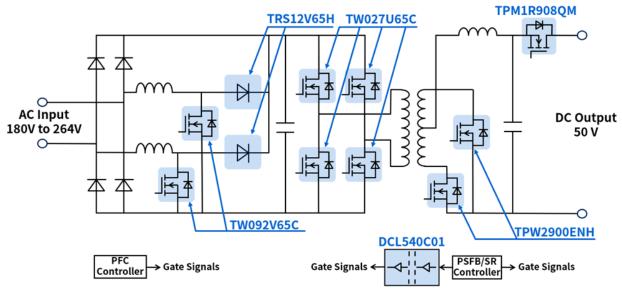




Fig. 2.1 Block Diagram

2.3. Appearance

Fig. 2.2 shows the appearance of this design.

This design consists of a Main board, a PFC board, and two PSFB boards.

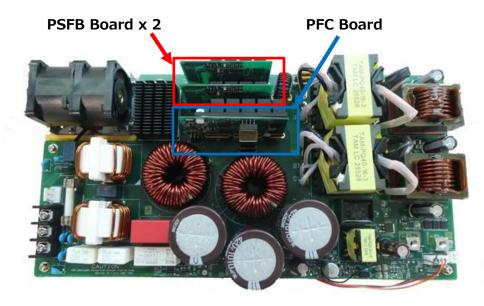


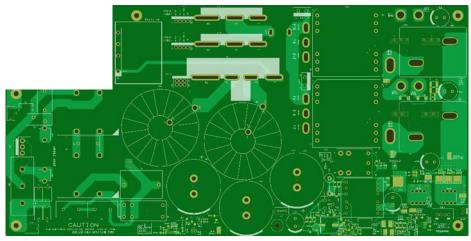
Fig. 2.2 External View of This Design

External Dimensions: 300mm x 150mm x 54mm



2.4. PCB Component Layout

Fig. 2.3 shows the component layout of the main board, Fig. 2.4 shows the component layout of the PFC board, Fig. 2.5 shows the component layout of the PSFB board.



<Front>

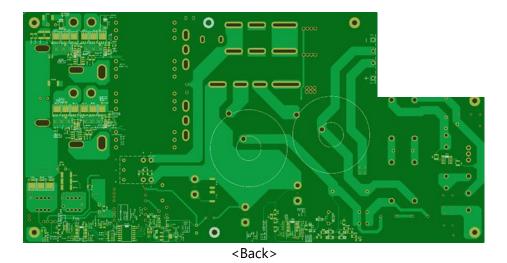
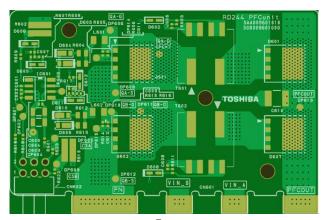


Fig. 2.3 Component Layout of Main Board





<Front>

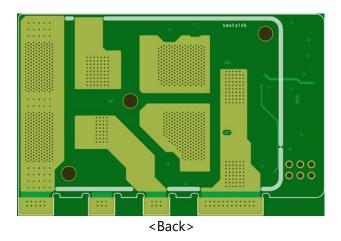
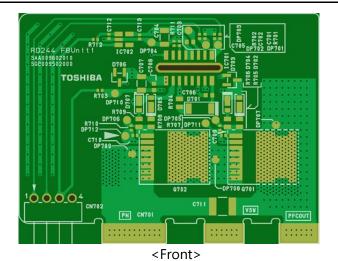


Fig. 2.4 Component Layout of PFC Board





Heet sink < Back >

Fig. 2.5 Component Layout of PSFB Board



3. Schematic, Bill of Materials, and PCB Pattern Diagram

3.1. Schematic

Refer to following files:

Main board: RD265-SCHEMATIC1-xx.pdf PFC board: RD265-SCHEMATIC2-xx.pdf PSFB board: RD265-SCHEMATIC3-xx.pdf

The same PSFB board is used twice.

(xx is the revision number.)

3.2. Bill of Materials

Refer to following files:

Main board: RD265-BOM1-xx.pdf PFC board: RD265-BOM2-xx.pdf PSFB board: RD265-BOM3-xx.pdf The same PSFB board is used twice.

(xx is the revision number.)

3.3. PCB Pattern Diagram

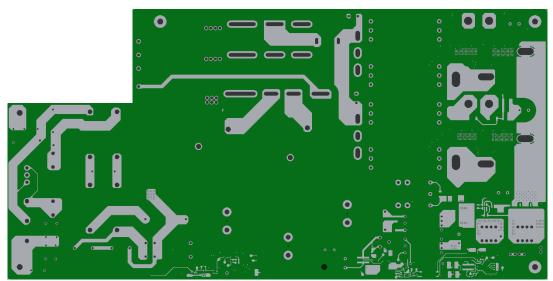
Fig. 3.1 shows PCB pattern diagram of the main board, Fig. 3.2 shows PCB pattern diagram of the PFC board, Fig. 3.3 shows PCB pattern diagram of the PSFB board.

Refer to following files:

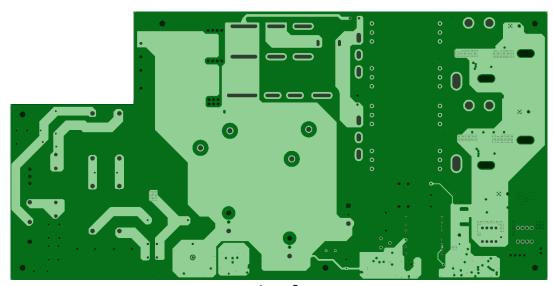
Main board: RD265-LAYER1-xx.pdf PFC board: RD265-LAYER2-xx.pdf PSFB board: RD265-LAYER3-xx.pdf The same PSFB board is used twice.

(xx is the revision number.)

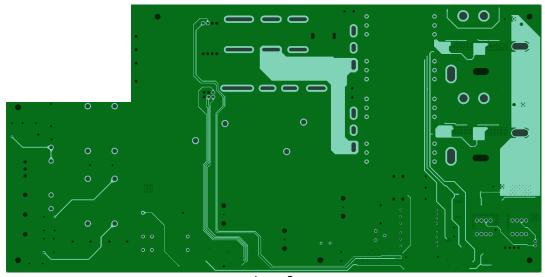




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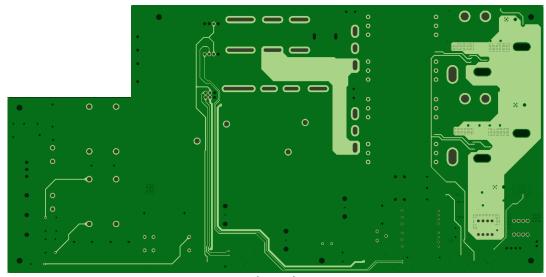


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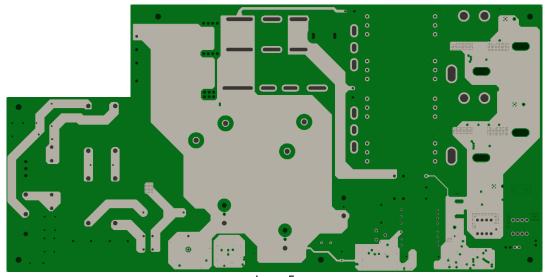


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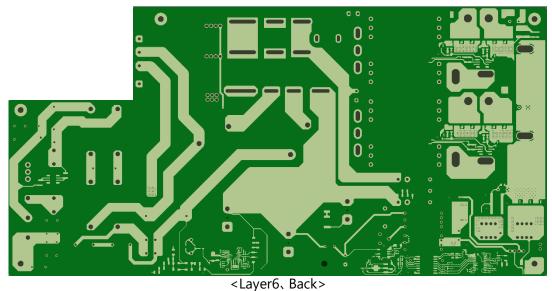




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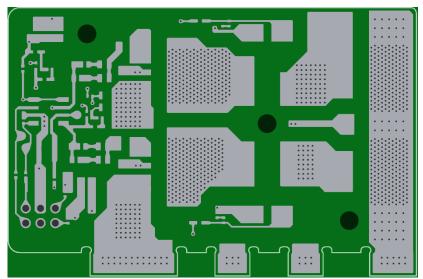
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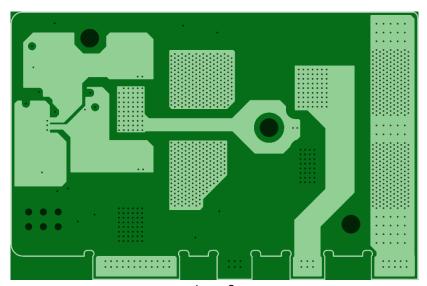
Layer or Backs

Fig. 3.1 Main Board Pattern Diagram (Front View)

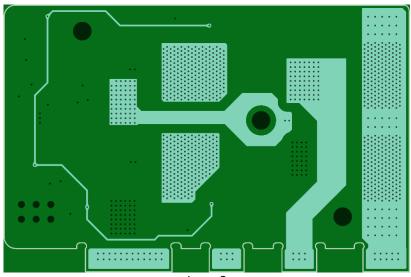




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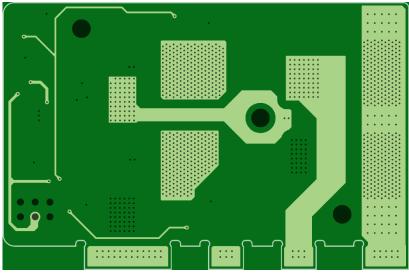


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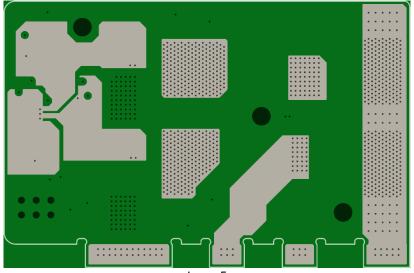


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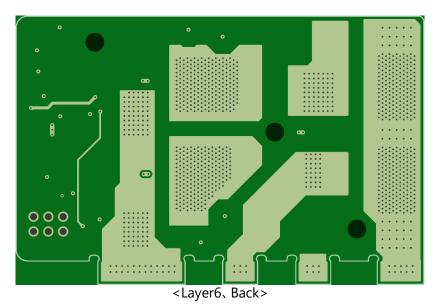
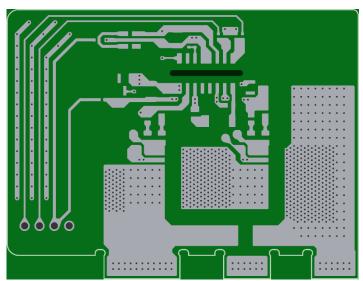
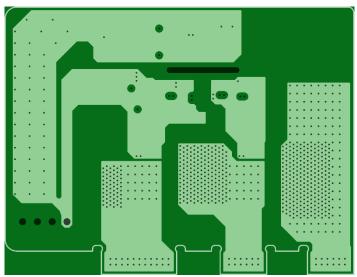


Fig. 3.2 PFC Board Pattern Diagram (Front View)

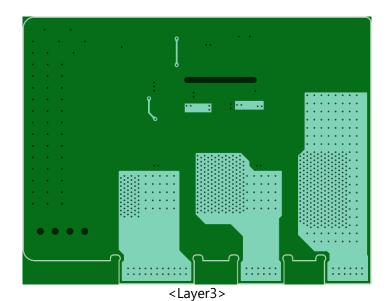




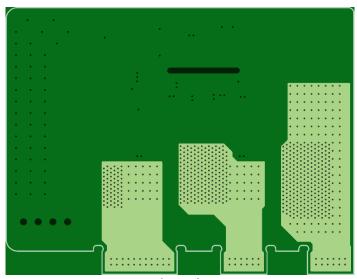
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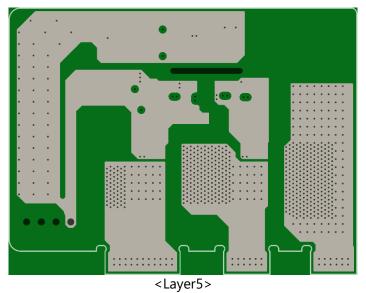
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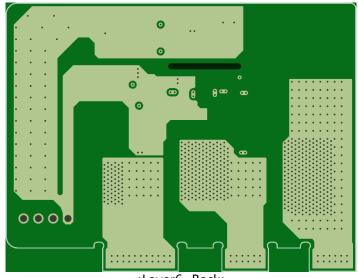






<Layer4>





<Layer6、Back>

Fig. 3.3 PSFB Board Pattern Diagram (Front View)



4. Operating Procedure

4.1. Connecting to an External Device

Fig. 4.2 shows the external connection terminals of this design. The area outlined in red indicates the AC input terminal (TB1), and the area outlined in blue indicates the DC output terminals (TB501, TB502). Connect the Neutral (N) side of the AC stabilized power supply to pin2 of TB1, connect the Live(L) of the AC stabilized power supply to pin1 of TB1. If necessary, connect the Earth (frame ground) to pin3 of TB1. Connect the positive side of the DC load to TB501, and the negative side to TB502. Please ensure that the power supply, load equipment, and cables used for connection meet the specifications of this power supply.



Fig. 4.2 External Connections

4.2. Start and Stop Procedures

Before starting the power supply, check that the input and output pin voltages are all OV.

[Starting Procedure]

1. Turn on the AC stabilized power supply.

[Stopping Procedure]

1. Turn off the AC stabilized power supply.

4.3. Evaluation Precautions (Electric Shock, Burn Injury, etc.)

Be careful of electric shock when connecting a stabilized power supply. Do not touch each part of the power supply directly while the power is on. Be very careful when observing the waveform. Even after this power supply is stopped, there is a risk of electric shock due to the remained charge of various capacitors. Confirm that the voltage of each part has decreased sufficiently before touching the board.

In addition, the semiconductor or inductor of this power supply generates heat according to the load current. Do not touch each part of the power supply while the power supply is in operation, as there is a risk of burns.



5. Power Characteristics

The power supply efficiency measurement results of this design are described below.

5.1. Efficiency

The power supply efficiency measurement results of this design are shown below. Measurements were conducted with the output voltage of the AC stabilized power supply set to 230V.

Fig. 5.1 shows the results when the AC stabilized power supply is set to 230V. At 100% load power, this design achieves high efficiency of 94.8%.

The efficiency measurement at this time is performed with the cooling FAN driven by an external power supply. The measurement result changes when the cooling FAN is driven by the internal power supply. In addition, this design equipped with the ORing circuit at the output section. When ORing circuit is removed, the power supply efficiency of this design will be improved.

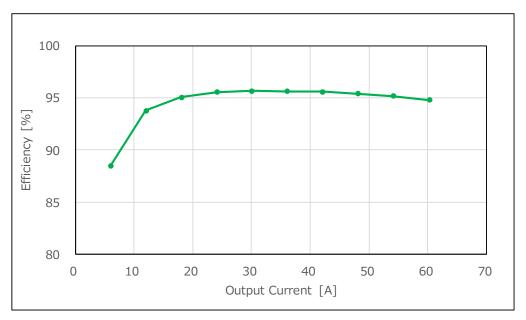


Fig. 5.1 Efficiency Measurement Results ($V_{in} = 230V$)

For reference, Fig. 5.2 to Fig. 5.3 show the measurement efficiency of this design and the standard of 80 PLUS. It is confirmed that the efficiency of this design in Vin = 230V meets Platinum standard. The 80 PLUS standards in the chart are as of September 2025. The standard values may be updated. Please check them every time. This design is not certified for 80 PLUS. It is necessary to measure the power supply efficiency using the equipment that will be the final product and acquire the certification.



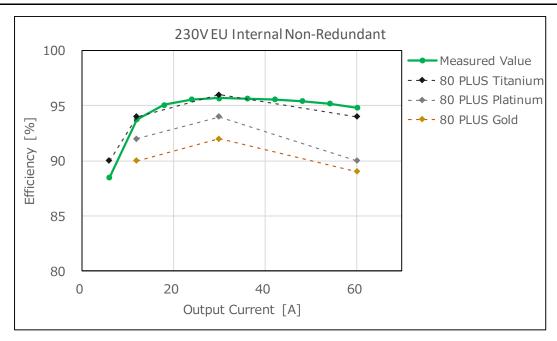


Fig.5.2 Efficiency Measurement Result (80 PLUS 230V EU Internal Non-Redundant)

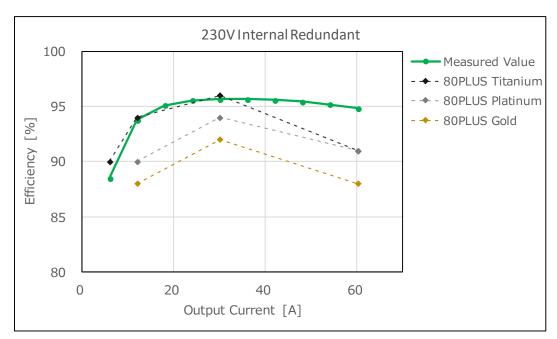


Fig.5.3 Efficiency Measurement Result (80 PLUS 230V Internal Redundant)



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